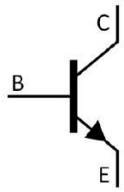
TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

h_{FE},

Low noise, high h_{FE}, high breakdown voltage.

Low noise audio amplifier application.





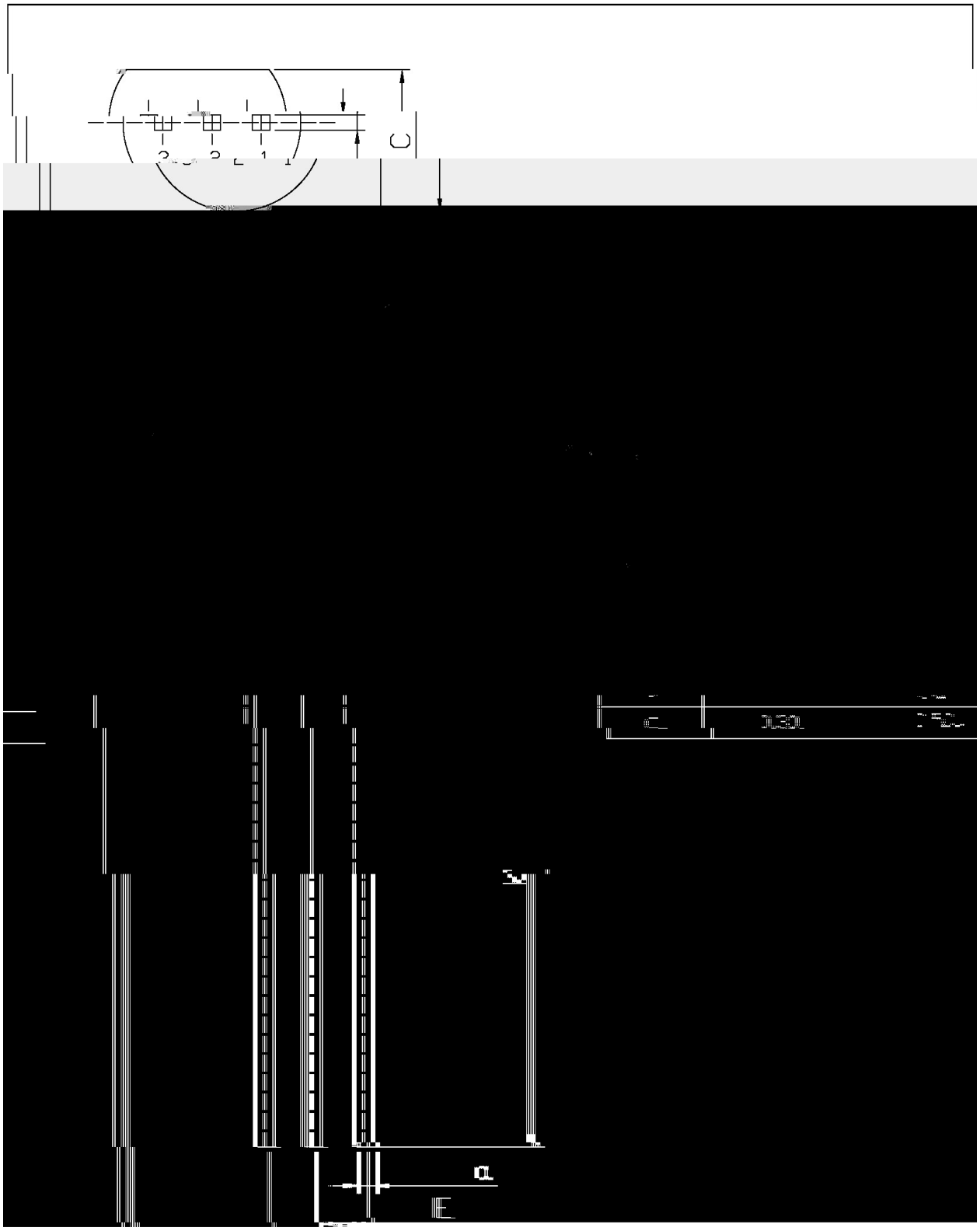
PIN1 Base PIN 2 Collector PIN 3 Emitter

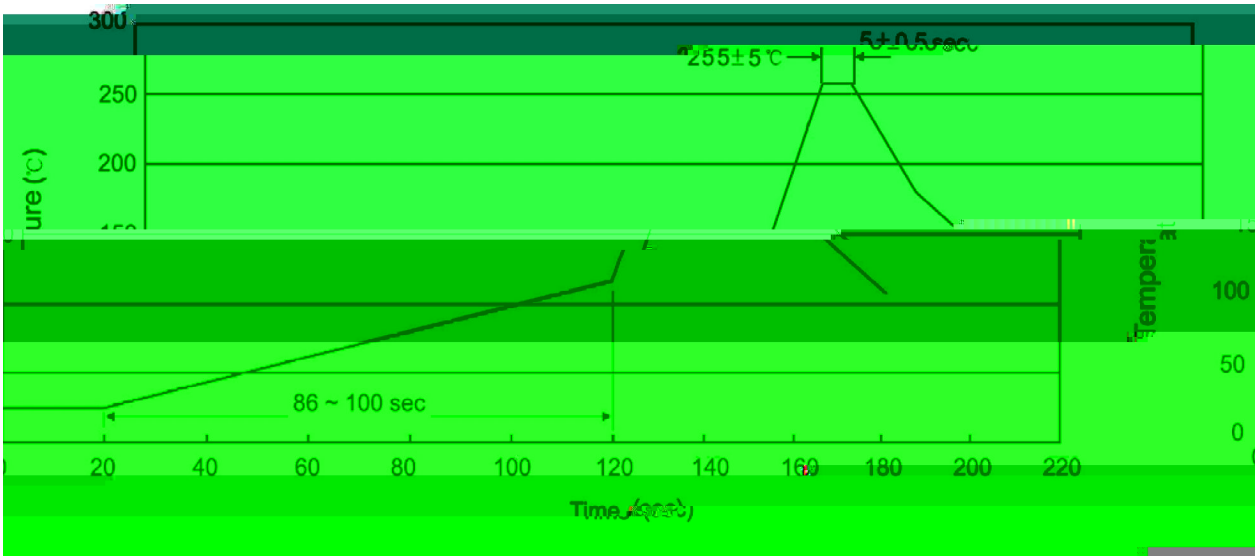
h_{FE} Classifications Symbol	Y	GR	BL
h_{FE} Range	120~240	200~400	350~700

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1.0mA I_B=0	120			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=100μA I_E=0	120			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	5.0			V
Collector Cut-Off Current	I					

TO-92 Unit: mm





				Note:	
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375